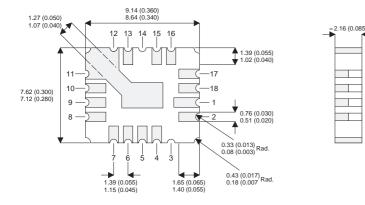


MECHANICAL DATA Dimensions in mm (inches)



### LCC4

GATE	Pins 4,5
DRAIN	Pins1,2,15,16,17,18
SOURCE	Pins 6,7,8,9,10,11,12,13

# P-CHANNEL POWER MOSFET

V <sub>DSS</sub>	-100V
I <sub>D(cont)</sub>	-3.5A
R <sub>DS(on)</sub>	0.6Ω

### FEATURES

- SURFACE MOUNT
- SMALL FOOTPRINT
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- AVALANCHE ENERGY RATING
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C unless otherwise stated)

		,
V <sub>GS</sub>	Gate – Source Voltage	±20V
I <sub>D</sub>	Continuous Drain Current $(V_{GS} = -10V, T_{case} = 25^{\circ}C)$	-3.5A
I <sub>D</sub>	Continuous Drain Current $(V_{GS} = -10V, T_{case} = 100^{\circ}C)$	-2.2A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	-14A
PD	Power Dissipation @ T <sub>case</sub> = 25°C	14W
	Linear Derating Factor	0.09W/°C
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>2</sup>	115mJ
dv/dt	Peak Diode Recovery <sup>3</sup>	-5.0V/ns
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Temperature Range	-55 to +150°C
Ū	Surface Temperature (for 5 sec).	300°C

#### Notes

1) Pulse Test: Pulse Width  $\leq$  300 $\mu$ s,  $\delta \leq$  2%

2) @ V\_DD = -25V , Peak I\_L = -3.5A , Starting T\_J = 25°C

3) @ I\_{SD}  $\leq$  -3.5A , di/dt  $\leq$  -110A/µs , V\_{DD}  $\leq$  BV\_{DSS} , T\_J  $\leq$  150°C , Suggested R\_G = 7.5\Omega

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

## 2N6845LCC4 IRFE9120



# 2N6845LCC4 IRFE9120

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
	STATIC ELECTRICAL RATINGS		•			-	
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = -1mA$	-100			V	
$\Delta BV_{DSS}$	3 Temperature Coefficient of	Reference to 25°C		-0.10		V/°C	
$\Delta T_{J}$	Breakdown Voltage	I <sub>D</sub> = -1mA		-0.10		V/ C	
D	Static Drain – Source On–State	$V_{GS} = -10V$ $I_{D} = -2.2A$			0.6	Ω	
R <sub>DS(on)</sub>	Resistance <sup>1</sup>	$V_{GS} = -10V$ $I_{D} = -3.5A$			0.69		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = -250\mu$	A -2		-4	V	
9 <sub>fs</sub>	Forward Transconductance <sup>1</sup>	$V_{DS} \ge -15V$ $I_{DS} = -2.2A$	A 1.25			S(び)	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0$ $V_{DS} = -80^{\circ}$ $T_{J} = 125^{\circ}$			-25 -250	μA	
I <sub>GSS</sub>	Forward Gate – Source Leakage	V <sub>GS</sub> = -20V	-		-100		
I <sub>GSS</sub>	Reverse Gate – Source Leakage	V <sub>GS</sub> = 20V			100	nA	
000	DYNAMIC CHARACTERISTICS	00				<u> </u>	
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0		380		Τ	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -25V		170		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz		45		1 .	
Qg	Total Gate Charge	V <sub>GS</sub> = -10V			16.3	<u> </u>	
Q <sub>gs</sub>	Gate – Source Charge	I <sub>D</sub> = -3.5A			4.7	nC	
Q <sub>gd</sub>	Gate – Drain ("Miller") Charge	V <sub>DS</sub> = -50V			9.0		
t <sub>d(on)</sub>	Turn–On Delay Time				60		
t <sub>r</sub>	Rise Time	$V_{DD} = -50V$			100		
t <sub>d(off)</sub>	Turn–Off Delay Time	$I_{D} = -3.5A$ $R_{G} = 7.5\Omega$		50	– ns		
t <sub>f</sub>	Fall Time				70	1	
	SOURCE – DRAIN DIODE CHARAC	TERISTICS	•	I		<u> </u>	
I <sub>S</sub>	Continuous Source Current				-3.5		
I <sub>SM</sub>	Pulse Source Current <sup>2</sup>				-14	A	
V <sub>SD</sub>	Diode Forward Voltage <sup>1</sup>	$I_{S} = -3.5A$ $T_{J} = 25^{\circ}C$ $V_{GS} = 0$			-4.8	V	
t <sub>rr</sub>	Reverse Recovery Time	$I_{\rm F} = -3.5$ A $T_{\rm J} = 25^{\circ}$ C			200	ns	
Q <sub>rr</sub>	Reverse Recovery Charge <sup>1</sup>	d <sub>i</sub> / d <sub>t</sub> ≤ -100A/µs V <sub>DD</sub> ≤ -50 <sup>v</sup>	v		3.1	μC	
t <sub>on</sub>	Forward Turn-On Time			Negligible		1	
	THERMAL CHARACTERISTICS	·	•			<u> </u>	
$R_{ extsf{ heta}JC}$	Thermal Resistance Junction – Case				9.1 26 °C/W		
$R_{\theta JPC}$	Thermal Resistance Junction – PC Bo	bard					

#### Notes

1) Pulse Test: Pulse Width  $\leq$  300ms,  $\delta \leq$  2%

2) Repetitive Rating - Pulse width limited by maximum junction temperature.

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